

# TPCM8102

Lithium Ion Battery Applications  
 Notebook PC Applications  
 Portable Equipment Applications

- Small footprint due to a small and thin package
- Low drain-source ON-resistance:  $R_{DS(ON)} = 6.0 \text{ m}\Omega$  (typ.)
- High forward transfer admittance:  $|Y_{fs}| = 44\text{S}$  (typ.)
- Low leakage current:  $I_{DSS} = -10 \text{ }\mu\text{A}$  (max) ( $V_{DS} = -30 \text{ V}$ )
- Enhancement mode:  $V_{th} = -0.8 \text{ to } -2.0 \text{ V}$  ( $V_{DS} = -10 \text{ V}$ ,  $I_D = -1 \text{ mA}$ )

### Absolute Maximum Ratings ( $T_a = 25^\circ\text{C}$ )

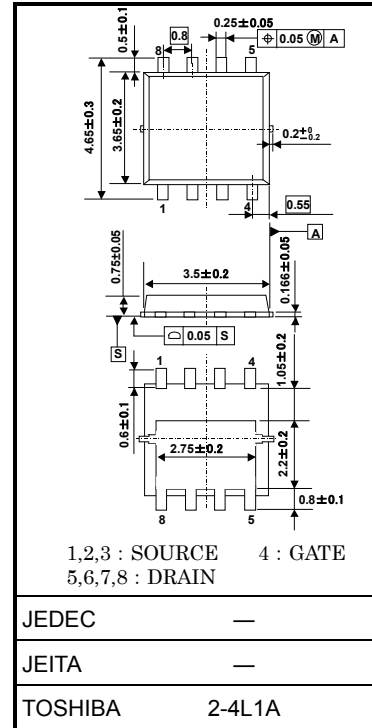
Characteristic	Symbol	Rating	Unit	
Drain-source voltage	$V_{DSS}$	-30	V	
Drain-gate voltage ( $R_{GS} = 20 \text{ k}\Omega$ )	$V_{DGR}$	-30	V	
Gate-source voltage	$V_{GSS}$	$\pm 20$	V	
Drain current	DC (Note 1)	$I_D$	-25	A
	Pulse (Note 1)	$I_{DP}$	-75	
Drain power dissipation ( $T_c = 25^\circ\text{C}$ )	$P_D$	30	W	
Drain power dissipation ( $t = 10 \text{ s}$ ) (Note 2a)	$P_D$	2.3	W	
Drain power dissipation ( $t = 10 \text{ s}$ ) (Note 2b)	$P_D$	1.0	W	
Single-pulse avalanche energy (Note 3)	$E_{AS}$	81	mJ	
Avalanche current	$I_{AR}$	-25	A	
Repetitive avalanche energy ( $T_c = 25^\circ\text{C}$ ) (Note 4)	$E_{AR}$	1.8	mJ	
Channel temperature	$T_{ch}$	150	$^\circ\text{C}$	
Storage temperature range	$T_{stg}$	-55 to 150	$^\circ\text{C}$	

Note: For Notes 1 to 4, refer to the next page.

Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings. Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/Derating Concept and Methods) and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

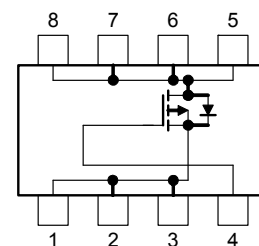
This transistor is an electrostatic-sensitive device. Handle with care.

Unit: mm



Weight: 0.028 g (typ.)

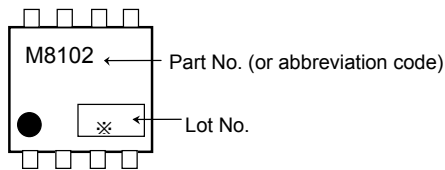
### Circuit Configuration



## Thermal Characteristics

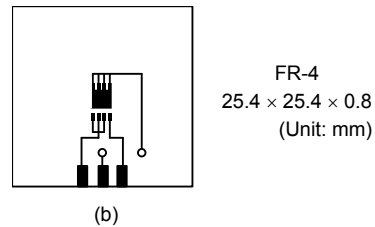
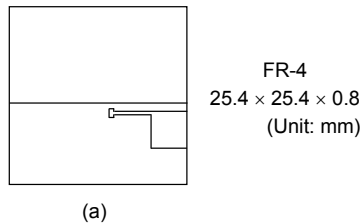
Characteristic	Symbol	Max	Unit
Thermal resistance, channel to case ( $T_c = 25^\circ\text{C}$ )	$R_{th(ch-c)}$	4.17	$^\circ\text{C/W}$
Thermal resistance, channel to ambient ( $t = 10\text{ s}$ ) (Note 2a)	$R_{th(ch-a)}$	54.3	$^\circ\text{C/W}$
Thermal resistance, channel to ambient ( $t = 10\text{ s}$ ) (Note 2b)	$R_{th(ch-a)}$	125	$^\circ\text{C/W}$

## Marking (Note 5)



Note 1: Ensure that the channel temperature does not exceed  $150^\circ\text{C}$ .

Note 2: (a) Device mounted on a glass-epoxy board (a) (b) Device mounted on a glass-epoxy board (b)

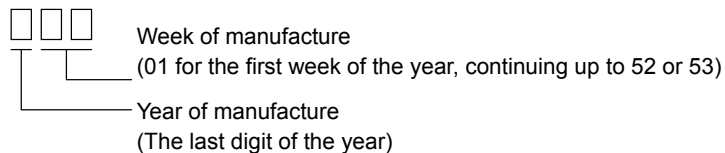


Note 3:  $V_{DD} = -24\text{ V}$ ,  $T_{ch} = 25^\circ\text{C}$  (initial),  $L = 100\mu\text{H}$ ,  $R_G = 25\ \Omega$ ,  $I_{AR} = -25\text{ A}$

Note 4: Repetitive rating: pulse width limited by max channel temperature

Note 5: • on lower left of the marking indicates Pin 1.

\* Weekly code: (Three digits)

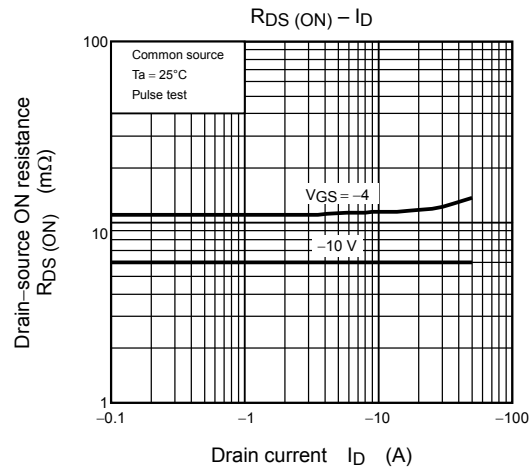
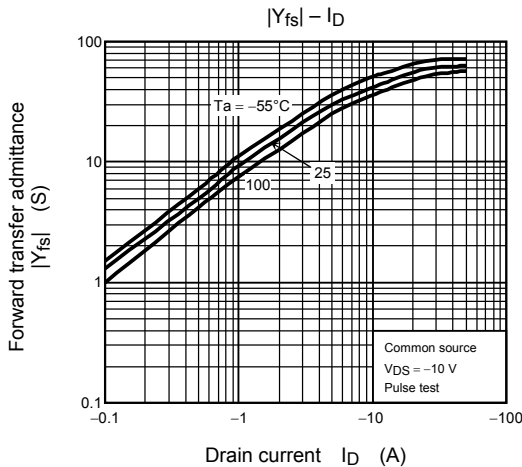
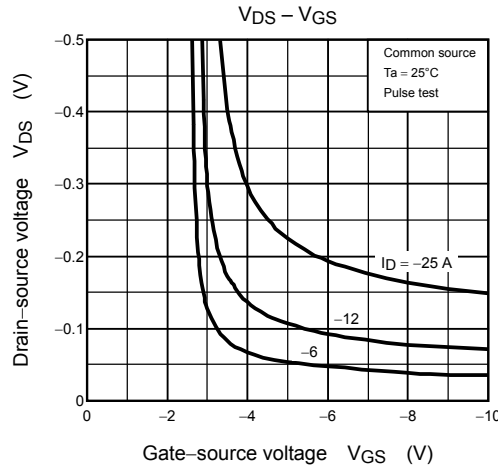
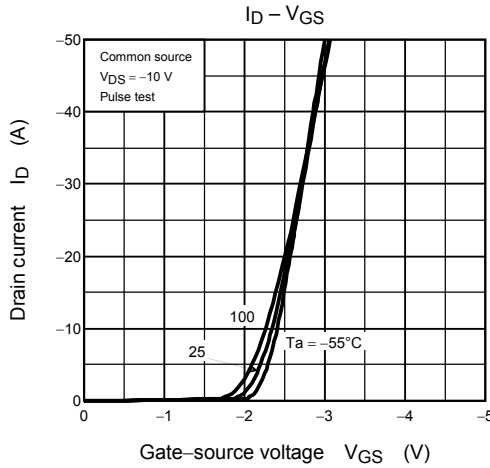
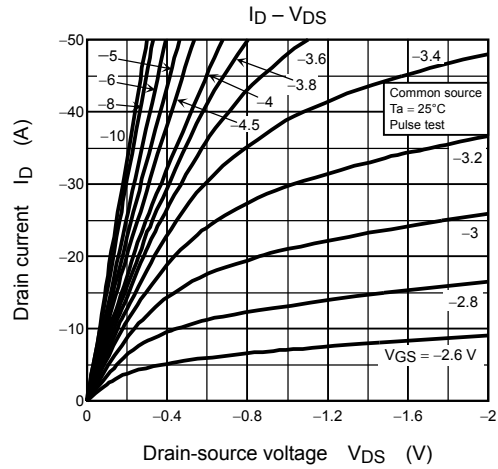
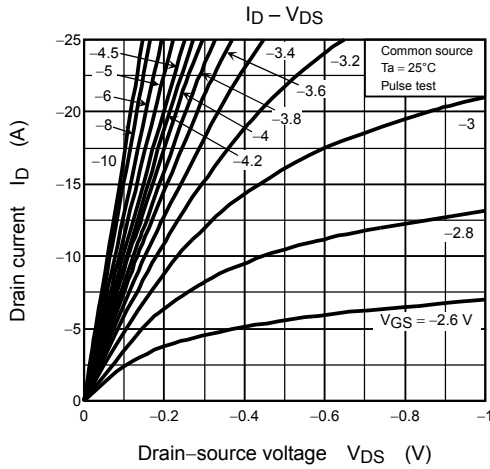


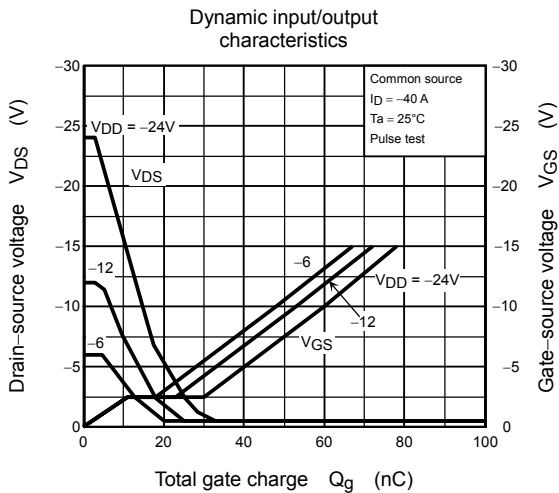
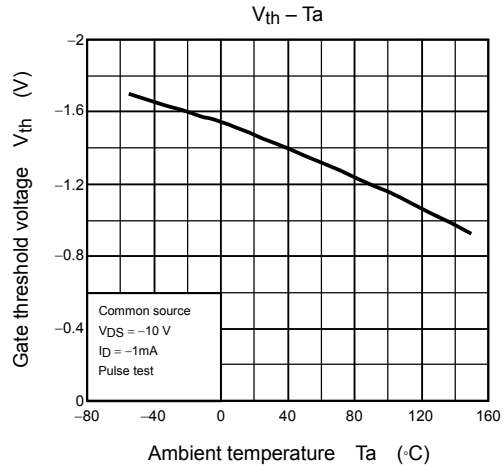
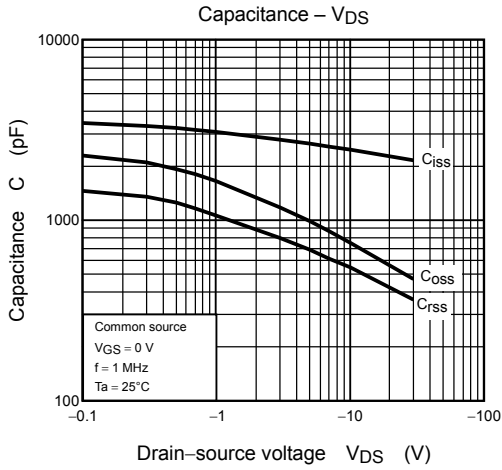
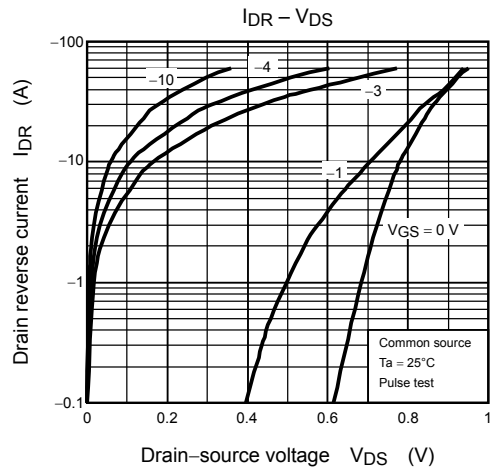
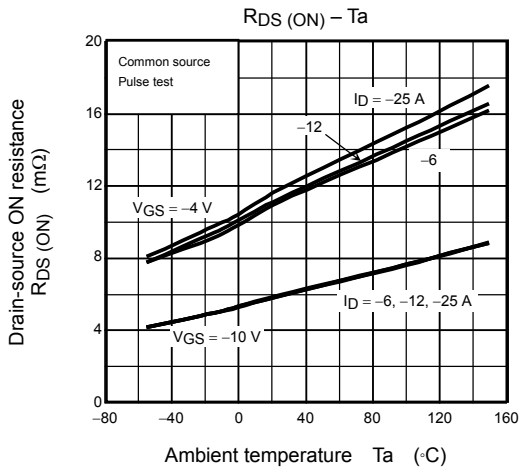
## Electrical Characteristics (Ta = 25°C)

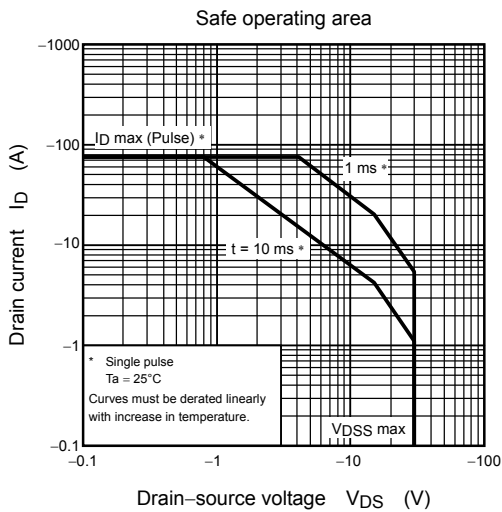
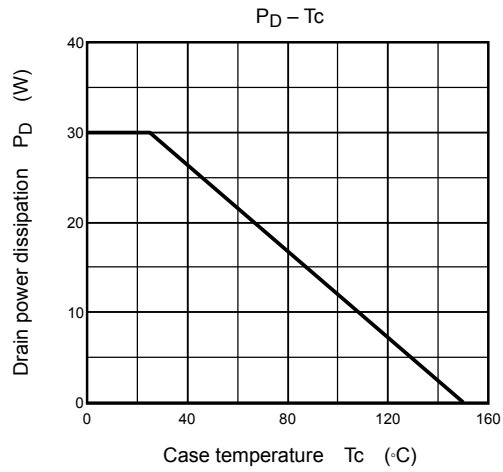
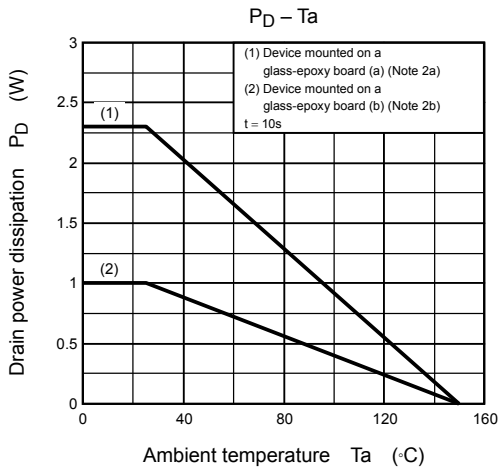
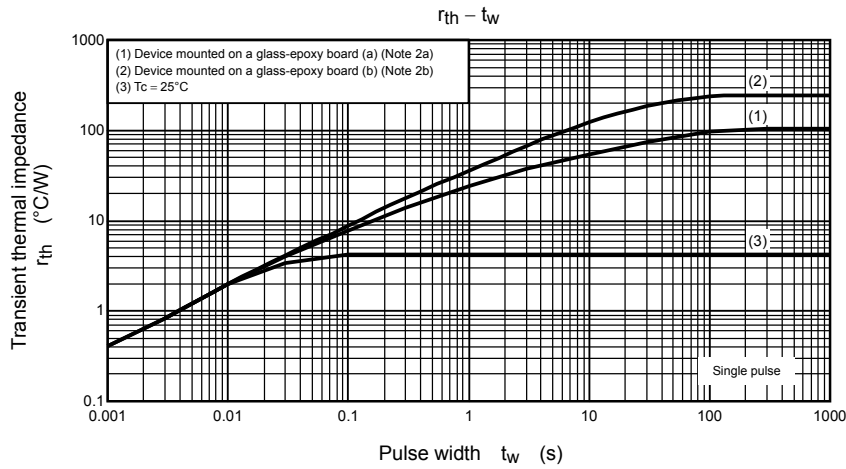
Characteristic		Symbol	Test Condition	Min	Typ.	Max	Unit
Gate leakage current		$I_{GSS}$	$V_{GS} = \pm 20 \text{ V}, V_{DS} = 0 \text{ V}$	—	—	$\pm 100$	nA
Drain cutoff current		$I_{DSS}$	$V_{DS} = -30 \text{ V}, V_{GS} = 0 \text{ V}$	—	—	-10	$\mu\text{A}$
Drain-source breakdown voltage		$V_{(BR) DSS}$	$I_D = -10 \text{ mA}, V_{GS} = 0 \text{ V}$	-30	—	—	V
		$V_{(BR) DSX}$	$I_D = -10 \text{ mA}, V_{GS} = 20 \text{ V}$	-13	—	—	
Gate threshold voltage		$V_{th}$	$V_{DS} = -10 \text{ V}, I_D = -1 \text{ mA}$	-0.8	—	-2.0	V
Drain-source ON-resistance		$R_{DS(ON)}$	$V_{GS} = -4 \text{ V}, I_D = -12 \text{ A}$	—	11	16	m $\Omega$
			$V_{GS} = -10 \text{ V}, I_D = -12 \text{ A}$	—	6.0	7.7	
Forward transfer admittance		$ Y_{fs} $	$V_{DS} = -10 \text{ V}, I_D = -12 \text{ A}$	22	44	—	S
Input capacitance		$C_{iss}$	$V_{DS} = -10 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$	—	2450	—	pF
Reverse transfer capacitance		$C_{rss}$		—	530	—	
Output capacitance		$C_{oss}$		—	740	—	
Switching time	Rise time	$t_r$	<p><math>V_{GS} = 0 \text{ V}</math> <math>V_{GS} = -10 \text{ V}</math> <math>I_D = -12 \text{ A}</math> <math>V_{OUT}</math> <math>4.7 \Omega</math> <math>R_L = 1.25 \Omega</math> <math>V_{DD} \approx -15 \text{ V}</math> Duty <math>\leq 1\%</math>, <math>t_w = 10 \mu\text{s}</math></p>	—	13	—	ns
	Turn-on time	$t_{on}$		—	22	—	
	Fall time	$t_f$		—	145	—	
	Turn-off time	$t_{off}$		—	340	—	
Total gate charge (gate-source plus gate-drain)		$Q_g$	$V_{DD} \approx -24 \text{ V}, V_{GS} = -10 \text{ V}, I_D = -25 \text{ A}$	—	60	—	nC
Gate-source charge 1		$Q_{gs1}$		—	11	—	
Gate-drain ("Miller") charge		$Q_{gd}$		—	19	—	

## Source-Drain Ratings and Characteristics (Ta = 25°C)

Characteristic		Symbol	Test Condition	Min	Typ.	Max	Unit
Drain reverse current	Pulse (Note 1)	$I_{DRP}$	—	—	—	-75	A
Forward voltage (diode)		$V_{DSF}$	$I_{DR} = -25 \text{ A}, V_{GS} = 0 \text{ V}$	—	—	1.2	V







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20070701-EN GENERAL

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